



### 30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-35 A

#### **Features**

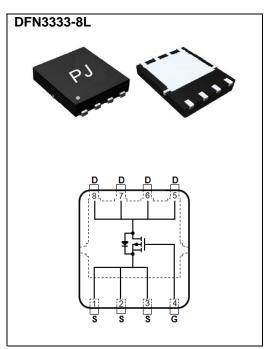
- $R_{DS(ON)}$ ,  $V_{GS}@-10V$ , $I_D@-10A<15.5m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-4.5V,I<sub>D</sub>@-6A<23mΩ
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-30	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	Tc=25°C	l <sub>D</sub>	-35	А	
	T <sub>C</sub> =100°C		-22		
Pulsed Drain Current(Note 1)	Tc=25°C	I <sub>DM</sub>	-140		
Power Dissipation	T <sub>C</sub> =25°C	Po	30	W	
	Tc=100°C		11		
Continuous Drain Current	T <sub>A</sub> =25°C	Ι <sub>D</sub>	-9.8	Α	
	T <sub>A</sub> =70°C		-7.8		
Power Dissipation	T <sub>A</sub> =25°C	1	2.0	W	
Power Dissipation	T <sub>A</sub> =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	4.2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250uA	-1.0	-1.6	-2.5			
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-10A	-	12	15.5	mΩ		
		V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-6A	-	18	23			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1.0	uA		
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA		
Dynamic <sup>(Note 6)</sup>								
Total Gate Charge	Qg	V <sub>DS</sub> =-15V, I <sub>D</sub> =-8A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	15	-	nC		
Gate-Source Charge	Qgs		-	4	-			
Gate-Drain Charge	$Q_{gd}$		-	6	-			
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1730	-	pF		
Output Capacitance	Coss		-	180	-			
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	125	-			
Turn-On Delay Time	td <sub>(on)</sub>	\/ 4E\/ I- 4A	-	9	-			
Turn-On Rise Time	tr	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 1,2)	-	22	-	ns		
Turn-Off Delay Time	td <sub>(off)</sub>		-	60	-			
Turn-Off Fall Time	t <sub>f</sub>	(**************************************	-	14	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	Is		-	-	-35	А		
Diode Forward Current	IS							
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A,V <sub>GS</sub> =0V	-	-0.7	-1	V		

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

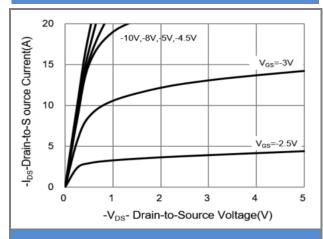
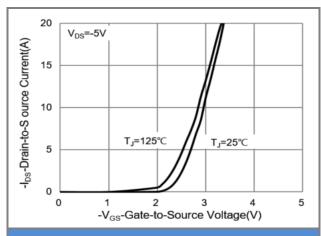


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

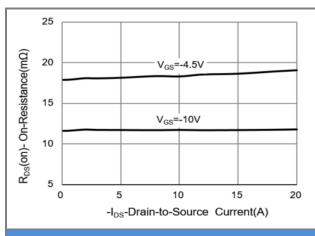


Fig.3 On-Resistance vs. Drain Current

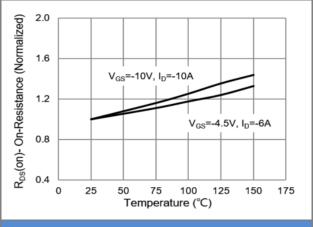


Fig.4 On-Resistance vs. Junction temperature

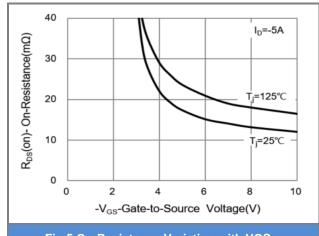


Fig.5 On-Resistance Variation with VGS.

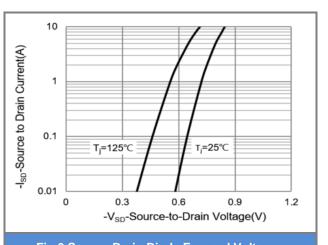


Fig.6 Source-Drain Diode Forward Voltage



1.2

1.0

8.0

0.6

0.4

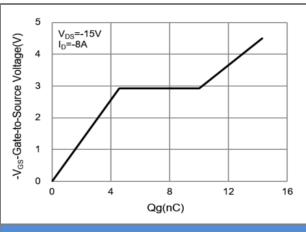
25

-V<sub>TH</sub>-G-S Vriance

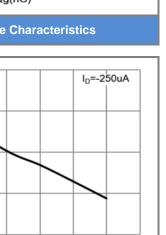


## **PJQ4403P**

#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 



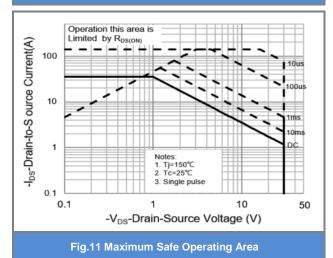
125

175

100

Temperature (°C)

Fig.9 Threshold Voltage Variation with Temperature



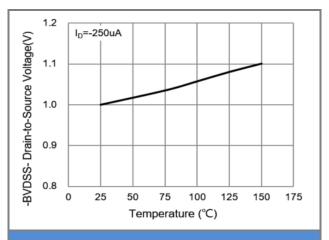


Fig.8 Breakdown Voltage Variation vs. Temperature.

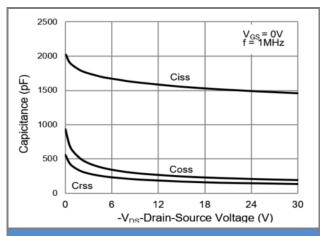


Fig.10 Capacitance vs. Drain-Source Voltage





#### **TYPICAL CHARACTERISTIC CURVES**

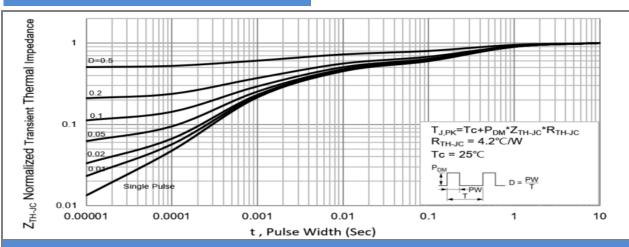


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

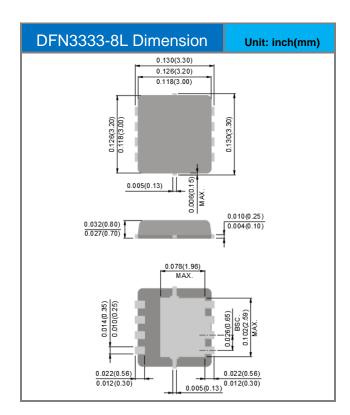


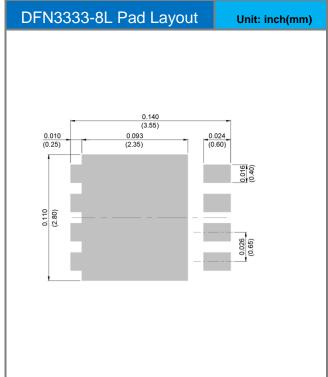


### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4403P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4403	Halogen free RoHS compliant

### **Packaging Information & Mounting Pad Layout**









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